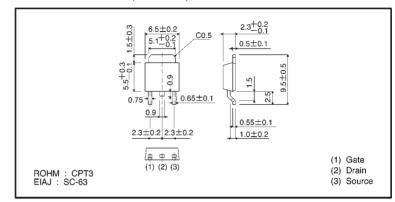
Switching (200V, 3A) **25K2887**

Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Gate-source voltage (Vgss) guaranteed to be ±30V.
- 5) Easily designed drive circuits.
- 6) Easy to parallel.

●Structure Silicon N-channel MOSFET

External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		Voss	200	٧
Gate-source voltage		Vgss	±30	V
Dunin august	Continuous	ΙD	3	А
Drain current	Pulsed	lpp*	12	А
Reverse drain	Continuous	IDR	3	Α
current	Pulsed	lorp*	12	Α
Total power dissipation (Tc=25℃)		Po	20	W
Channel temperature		Tch	150	ొ
Storage temperature		Tstg	−55~ +150	င

^{*} Pw \leq 10 μ s, Duty cycle \leq 1%

Packaging specifications

	Package	Taping
Туре	Code	TL
	Basic ordering unit (pieces)	2500
2SK2887		0



Transistors 2SK2887

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Gate-source leakage	lass			±100	nA	V _{GS} =±30V, V _{DS} =0V
Drain-source breakdown voltage	V(BR)DSS	200	_	_	٧	ID=1mA, VGS=0V
Zero gate voltage drain current	loss	_	_	100	μΑ	V _{DS} =200V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	2.0	_	4.0	٧	V _{DS} =10V, I _D =1mA
Static drain-source on-state resistance	RDS(on)	_	0.7	0.9	Ω	In=1.5A, Vgs=10V
Forward transfer admittance	Yfs	0.6	1.5	_	S	In=1.5A, Vns=10V
Input capacitance	Ciss	_	230	_	pF	V _{DS} =10V
Output capacitance	Coss	_	100	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	_	35	_	pF	f=1MHz
Turn-on delay time	td(on)	_	10	_	ns	I _D =1.5A, V _{DD} ≒100V
Rise time	tr	_	12	_	ns	V _{GS} =10V
Turn-off delay time	td(off)	_	26	_	ns	RL=68 Ω
Fall time	t _f	_	34	_	ns	R _G =10Ω
Reverse recovery time	trr	_	96	_	ns	IDR=3A, VGS=0V
Reverse recovery charge	Qrr	_	0.59	_	μC	di/dt=100A/ μs

•Electrical characteristic curves

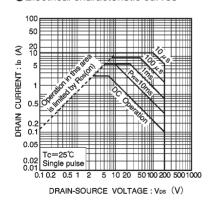


Fig.1 Maximum safe operating area

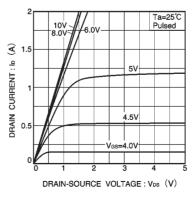


Fig.2 Typical output characteristics

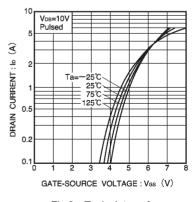


Fig.3 Typical transfer characteristics

Transistors 2SK2887

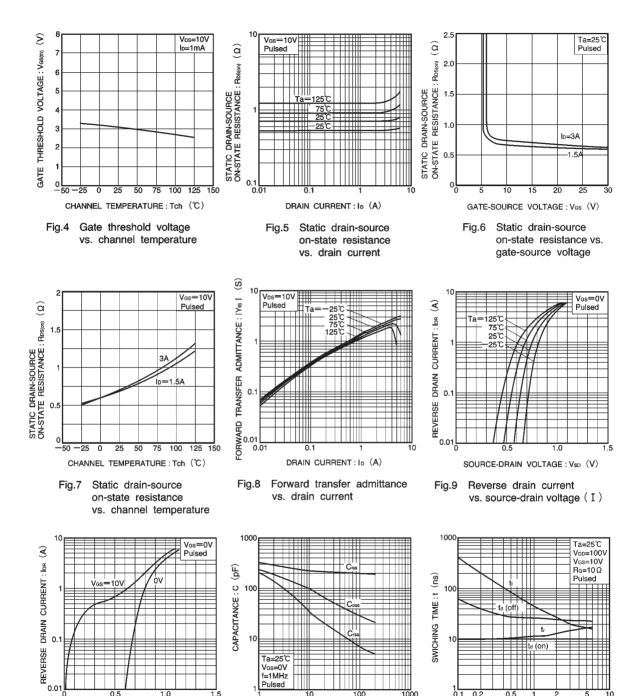


Fig.10 Reverse drain current vs. source-drain voltage (II)

SOURCE-DRAIN VOLTAGE: Vsp (V)

0.5

Fig.11 Typical capacitance vs. drain-source voltage

DRAIN-SOURCE VOLTAGE: VDS (V)

100

1000

Fig.12 Switching characteristics (See Figures 16 and 17 for the measurement circuit and resultant waveforms)

DRAIN CURRENT: Io (A)

0.5

0.1

0.2

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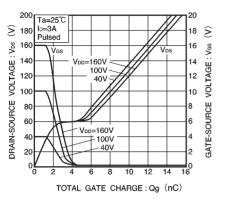


Fig.13 Dynamic input characteristics (See Figure 18 for measurement circuit)

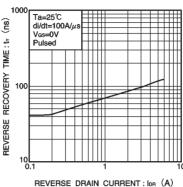


Fig.14 Reverse recovery time vs. reverse drain current

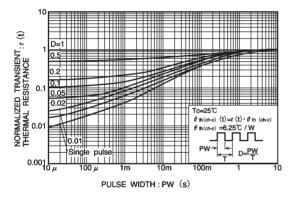
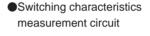


Fig.15 Normalized transient thermal resistance vs. pulse width



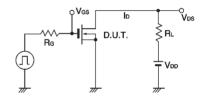


Fig.16 Switching time measurement circuit

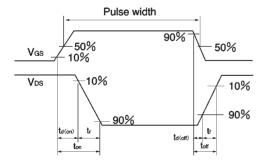


Fig.17 Switching time waveforms

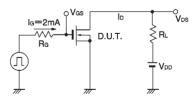


Fig.18 Gate charge time measurement circuit

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